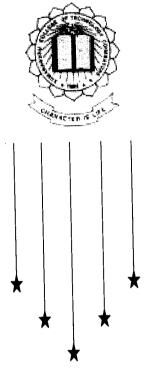
# MICROCONTROLLER BASED HIGH FREQUENCY INVERTER



2002-2003

**Project Report** 2002-2003

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## **Synopsis**

The demand for control of electric power for motor drive systems and industrial applications has existed for many years. With the use of power electronic devices control of many applications has become easier.

An inverter is a power electronic system that converts a variable or fixed DC supply into a variable ac output. Inverters find wide applications in areas such as variable speed ac motor drives, induction heating, standby power supplies etc.

In our project we have implemented the basic inverter in a high frequency configuration. High frequency power has several advantages over the conventional power system in the fact that it helps to improve overall system efficiency, speed of operation and reducing the power elements used. Currently a maximum frequency of 250 Hz is can be generated using our hardware. Further improvements like increasing the maximum frequency can be easily done by minimal changes in hardware.

# **Contents**

# Acknowledgement Synopsis

Chapter 1	Introduction	
	1.1 Power supply	2
	1.2 AC-DC converter	3
	1.3 Inverter with Gate drive	3
	1.4 Control segement	4
	1.5 Display	4
	1.6 High frequency power	5
	1.7 Applications of high frequency power	5
Chapter 2	Basic Block Diagram	7
Chapter 3	Power Supply Module	
	3.1 Overview	10
	3.2 Features Of LM78XX	11
Chapter 4	Power Devices	
	4.1 MOSFET Specifications	13
	4.2 MOSFET Parameters	14

Chapter 5	Gate Drives	
	5.1 Gate Drive Requirements	17
	5.2 Gate Drive Selection	20
Chapter 6	Inverters	
	6.1 Overview	23
	6.2 Single Phase Inverter	24
	6.3 Three Phase Inverter	25
Chapter 7	Pulse Width Modulation	
	7.1 Overview	29
	7.2 Sinusoidal Pulse Width Modulation	30
Chapter 8	Display Module	
	8.1 BCD to Seven Segment Decoder	33
Chapter 9	Switching and Isolation	
	9.1 Digital/Analog Switches	36
	9.2 Optical Isolators	38
Chapter 10	Control Segment	
	10.1 Functional Block Diagram	41
	10.2 PIC 16F877 Architecture	42

Chapter 11	Software Routines	
	11.1 A/D Conversion and Interrupt	
	Servicing - Source Code	64
	11.2 Flowcharts for A/D conversion	
	and interrupt servicing	70
	11.3 PWM Routine – Source code	72
	11.4 Flowchart for PWM Operation	79
Chapter 12	Testing	81
Chapter 13	Conclusion	83
	Bibliography	85
	Appendix A: PIC 16F877	87
	Annendix B: Datasheets	92

Inverters are power electronic systems that convert a variable or fixed dc supply into a variable ac output. Inverters can be widely classified into two types:

- (i) Single phase inverters.
- (ii) Three phase inverters.

Each type can use controlled turn-on and turn-off switches likeBJTs, MOSFETs, IGBTs, MCTs, or GTOs. An inverter is called a voltage source inverter if the input voltage remains constant and a current source inverter if the input current is maintained constant.

The high frequency inverter consists of five basic segments.

They are:

- (i) Power supply segment
- (ii) AC-DC converter
- (iii) Inverter segment with gate drive
- (iv) Microcontroller with isolation segment
- (v) Display segment

#### 1.1 Power supply:

The power supply requirements for all the segments has been considered and the power supply suitably designed. There are a total of six separate DC regulated power supplies in this segment supplying the MOSFET gate drive circuit, the microcontroller and the display segment. The power supply uses a standard diode rectifier configuration along with a voltage regulator IC(LM 78xx) to produce a ripple free output.

#### 1.2 AC-DC converter:

The input for an inverter can be variable or fixed dc supply. Here a fixed dc supply is obtained by using a diode rectifier and s filtering capacitor to provide a constant voltage source.

## 1.3 Inverter segment with gate drive:

The inverter configuration is achieved by using a MOSFET H-Bridge. The MOSFETs used are standard N-Channel power MOSFETs. The MOSFETs are provided with separate floating grounds from separate sources to avoid 'Cross Conduction'. The gate drive is a simple, low impedance 'Totem Pole' TTL drive. The gate pulses to the MOSFETs are Pulse width modulated signals used to eliminate harmonics in the output stage.

#### 1.4 Microcontroller with Isolation:

The control circuitry utilizes the services of the RISC microcontroller. The controller used here is the PIC 16F877 manufactured by microchip. The microcontroller is isolated from

the power devices by using opto isolators. These provide excellent protection for the controller from the high voltages developed in the inverter stage.

## 1.5 Display segment:

The frequency set by the user is displayed using standard seven seven segment displays. The drive for these display segments is obtained from a BCD to Seven Segment display decoder/driver(74LS47). The decoder IC accepts bcd data and decodes them to be displayed in the display segments.

## 1.6 About High Frequency Power:

With the advent of power semiconductors many different frequency changers, namely static frequency changers have increasingly been employed in most industry and recently in homes and offices. Especially high frequency power can find applications such as motor drives, induction heating and fluorescent lighting.

By operating power systems at high frequency, the system can be made compact because of the large reduction in the size and weight of the transformers, reactors, capacitors and circuit breakers. Use of high frequency also speeds up system speed and provides high quality power. Moreover newly developed materials like amorphous metal and low dielectric loss materials can be more effectively than in a 50/60Hz power system.

It is important to select a proper frequency, which must take into account not only the requirements for much higher frequency from utilities but also the limits of the power elements. The following are the significant advantages to the utilization equipment that a high frequency system provides over a conventional 50/60Hz system.

- ✓ Large reduction in the size of transformers, reactors and electric machines, consequently resulting in improved efficiency and reduced cost of the electrical apparatus.
- ✓ Iron losses can be significantly reduced if amorphous materials are used for construction of reactors and transformer cores.
- ✓ Saving dielectric materials of capacitors, which make the capacitors compact and lower cost. Therefore loads with lower power factors can be economically used.
- ✓ The power source can offer an uninterrupted power supply by connecting some energy storage units to the power converter.
- ✓ Because the frequency is several times the conventional frequency the speed of electrical systems can be improved.

## 1.7 APPLICATIONS OF HIGH FREQUENCY POWER:

#### (a) High Speed Motors:

High speed motors find applications in various high power applications such as turbine compressors, and blowers for pipelines. Most of these high speed motors will have to use high frequency power to operate at such a large scale. These motors are compact and maintenance free.

#### (b)Induction Heating:

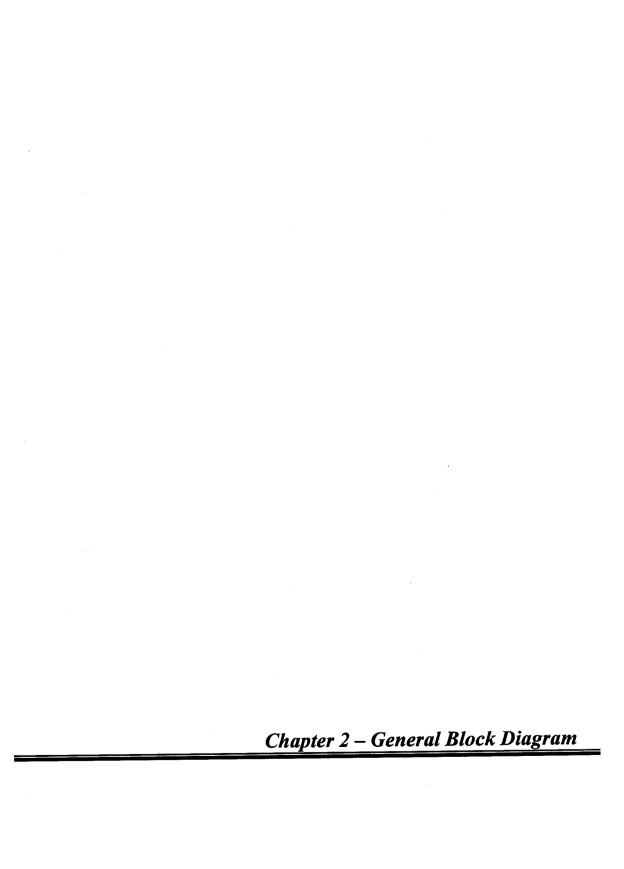
In Iron and Steel industry, high frequency power has been widely used for melting of cast steel and alloy in induction furnace, heating of steel bars and heat treatment of steel tubing and pipes by offering advantages of high efficiency, cleanliness, compactness of equipment and ease of control.

#### (c)Lighting Apparatus:

The use of high frequency supply to fluorescent and mercury lighting systems will result in dramatic reduction in size of size and improve system stability and efficiency. Moreover dimming of the lighting system becomes more easier and economical.

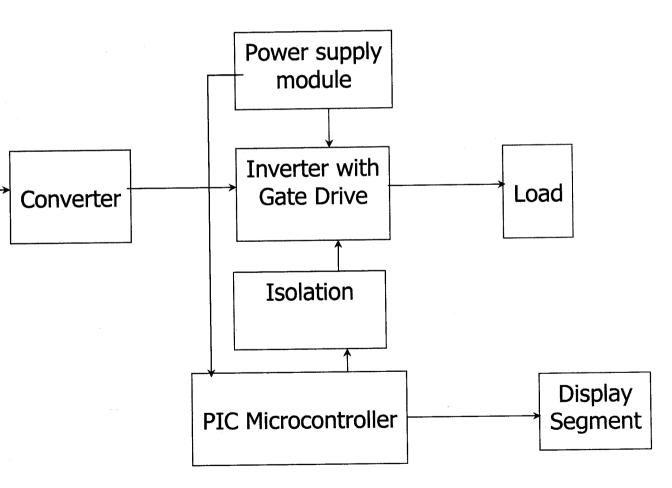
## (d)Quick Response DC Power Supply:

It is clear that high power and quick response dc power supply using thyristor converter is available only in high frequency power. Particularly quick response control of dc power supply is more easier.



## **Basic Block Diagram**

Fig 1



#### 3.1 Overview:

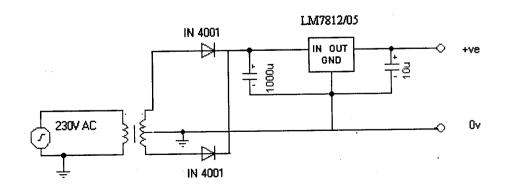
The power supply segment consists of six separate regulated power supplies. The design of six separate supplies was necessitated by the fact that the gate drives to the MOSFETs required separate floating grounds and that the microcontroller requires a different value of dc voltage for its operation.

The regulated power supply consists of the following key components:

- (i) Diode rectifier
- (ii) Capacitive filter at the input stage of the regulator
- (iii) Regulator IC(LM 78xx series)
- (iv) Capacitive filter at the output stage to reduce ripples.

The schematic of the individual power supplies in the module is shown below:

Fig 2





#### 3.2 Features of LM78XX:

One of the critical components used in the circuit is the LM 78xx series regulator IC. Some of the key features of the IC are:

- ➤ Effective improvement in output impedance of two orders of magnitude.
- > Output current of over 1.5A.
- ➤ Voltage tolerance of 5%.
- > Internal thermal overload protection.
- > Internal short circuit current limitation.
- > Linear positive regulator.

The choice of the power element used in the inverter is done under the following constraints:

- (i) High switching must be possible.
- (ii) Ease of gate drive.

Various choices are available for the power element to be used among which are SCRs, GTOs, IGBTs, SITs, BJTs, MOSFETs etc.. Among these options the thyristor family of devices is not suited for high switching speeds due to their commutation and device protection constraints. Among the power transistor family MOSFETs(Metal Oxide Semiconductor Field Effect Transistor) and IGBTs(Insulated Gate Bipolar transistors) are the best possible options. MOSFETs among the two are the ideal choice for high frequency inverters.

#### 4.1 MOSFET Specifications:

A power MOSFET is a voltage contolled device and requires only a small amount of input current. The switching speed is very high and the switching times are in the order of nanoseconds. MOSFETs are of two types, p-channel and n-channel. Either of these types can be used in the inverter but p-channel type is not preferable due to its considerable switching and conduction losses which is much higher than that of the n-channel type at high frequencies. The following requirements are essential for a switching device such as a MOSFET used in an inverter:

#### ❖ Dynamic dv/dt rating.

- \* Repetitive avalanche rating.
- ❖ Fast switching.
- ❖ Ease of gate drive.
- ❖ Ease of paralleling.
- ❖ Low ON resistance.
- ❖ Low thermal resistance.
- \* Rugged device design.

#### 4.2 MOSFET Parameters:

#### (i) Breakdown Voltage:

Breakdown voltage is the voltage at which the reverse-biased bodydrift diode breaks down and significant current starts to flow between the source and drain by the avalanche multiplication process, while the gate and source are shorted together.

#### (ii) Transconductance:

Transconductance, gfs, is a measure of the sensitivity of drain current to changes in gate-source bias. This parameter is normally quoted for a Vgs that gives a drain current equal to about one half of the maximum current rating value and for a VDS that ensures operation in the constant current region. Transconductance is influenced by gate width, which increases in proportion to the active area as cell density increases.

#### (iii) Threshold Voltage:

Threshold voltage, Vth, is defined as the minimum gate electrode bias required to strongly invert the surface under the poly and form a conducting channel between the source and the drain regions. Vth is usually measured at a drain-source current of  $250\mu A$ .

## (iv) Diode Forward Voltage:

The diode forward voltage, VF, is the guaranteed maximum forward drop of the body-drain diode at a specified value of source current.

#### (v) Power Dissipation:

The maximum allowable power dissipation that will raise the die allowable when the case temperature is held at 250C is important. It is give by Pd where:

$$P_{d} = \frac{T_{j\,m\,ax-25}}{R_{th}JC}$$

#### (vi) dv/dt Capability:

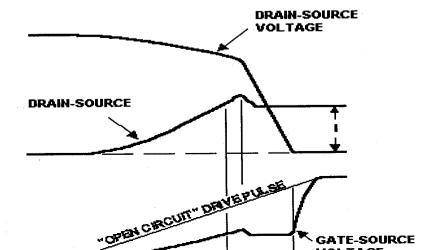
Peak diode recovery is defined as the maximum rate of rise of drain-source voltage allowed, i.e., dv/dt capability. If this rate is exceeded then the voltage across the gate-source terminals may become higher than the threshold voltage of the device, forcing the device into current conduction mode, and under certain conditions a catastrophic failure may occur.

#### 5.1 Requirements:

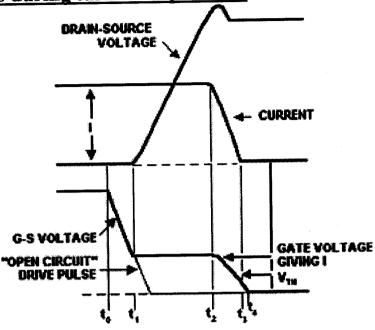
To turn on a power MOSFET a certain charge has to be supplied to the gate to raise it to the desired voltage, whether in the linear region, or in the "saturation" (fully enhanced) region. The best way to achieve this is by means of a voltage source, capable of supplying any amount of current in the shortest possible time. If the device is operated as a switch, a large transient current capability of the drive circuit reduces the time spent in the linear region, thereby reducing the switching losses.

On the other hand, if the device is operated in the linear mode, a large current from the gate drive circuit minimizes the relevance of the Miller effect, improving the bandwidth of the stage and reducing the harmonic distortion. The above considerations are more clearly understood by analyzing the MOSFET's ON-OFF waveforms shown below:

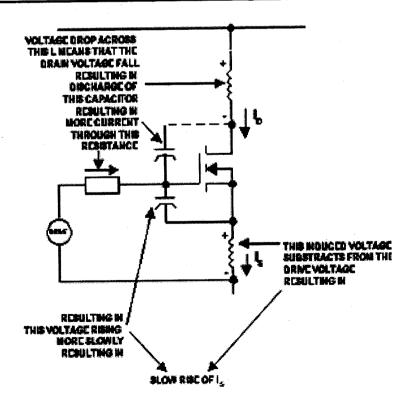
# Waveforms during turn-ON process: Fig 3



Waveforms during turn-OFF process:



# **Model of MOSFET during ON-OFF process:**



Care should be exercised not to exceed the gate-to-source maximum voltage rating. Even if the applied gate voltage is kept below the maximum rated gate voltage, the stray inductance of the gate connection, coupled with the gate capacitance, may generate ringing voltages that could lead to the destruction of the oxide layer. Overvoltages can also be coupled through the drain-gate self-capacitance due to transients in the drain circuit. A gate drive circuit with very low impedance insures that the gate voltage is not exceeded in normal operation.

From the model of the MOSFET during switching shown above, it is clear that 'Miller Effect' has an influence in the MOSFET switching process. It is explained as follows: During the period t1 to t2 some voltage is dropped across "unclamped" stray circuit inductance in series with the drain, and the drain-source voltage starts to fall. The decreasing drain-source voltage is reflected across the drain-gate capacitance, pulling a discharge current through it, and increasing the effective capacitive load on the drive circuit.

This in turn increases the voltage drop across the source impedance of the drive circuit, and decreases the rate of rise of voltage appearing between the gate and source terminals. Obviously, the lower the impedance of the gate drive circuit, the less this effect will be.

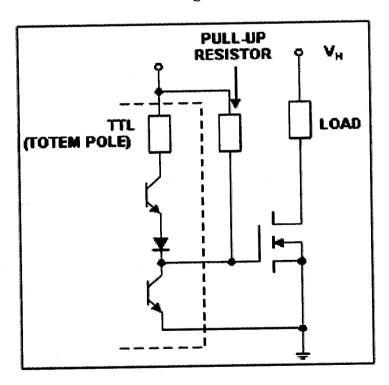
Similar considerations affect the turn-OFF process in MOSFETs, therefore it is critical to have low output impedance drive circuit, not only to reduce switching Losses, but also to clamp down unwanted transients from entering the gate.

## 5.2 Selection of gate drive:

Considering the factors mentioned in the previous chapter a TTL (Transistor Transistor Logic) 'totem pole' drive is suited because of its simplicity and low output impedance and high input impedance. The schematic is as shown below:

## TTL Totem Pole Drive:

Fig 6



With a gate charge of 60 nC and at a switching frequency is 100kHz, the power lost in the gate drive circuit is approximately:

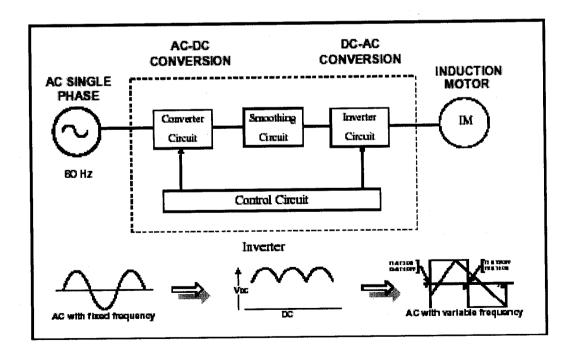
$$P = VGS \times QG \times f = 12 \times 60 \times 10-9 \times 100 \times 103 = 72 \text{mW}$$

The driver devices must be capable of supplying 1A without significant voltage drop, but hardly any power is dissipated in them. Whenever better switching performance is required, interface circuits should be added to provide fast current sourcing and sinking to the gate capacitances.

#### 6.1 Overview:

An inverter is the name given to a device that produces an AC, signal usually from a DC supply. Inverters are now commonplace in industry; their uses include, variable speed drives, induction heaters and uninterruptible power supply (UPS) systems. The basic block diagram is as shown:

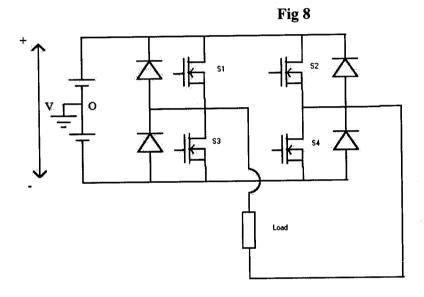
Fig 7



There are four main types of inverter; voltage source, current source, pulse width modulation (PWM) and the cycloconverter. Inverters can be broadly classified into two types, namely, single and three phase inverters.

#### 6.2 Single phase inverters:

The basic single phase inverter schematic is as shown:



In a single phase inverter two power electronic switches are conducting at any particular instant. In the schematic shown above, switches s1 and s4 are turned ON together while s2 and s3 are OFF. In one complete cycle s1 and s4 are ON for a specified duty cycle and s2 and s3 are ON for the remaining period in the same cycle. When the above method of operation is followed the output is as shown below:

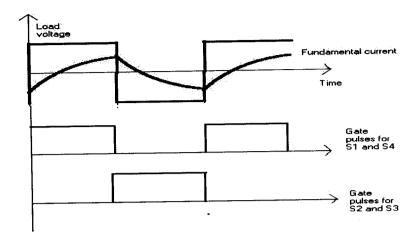


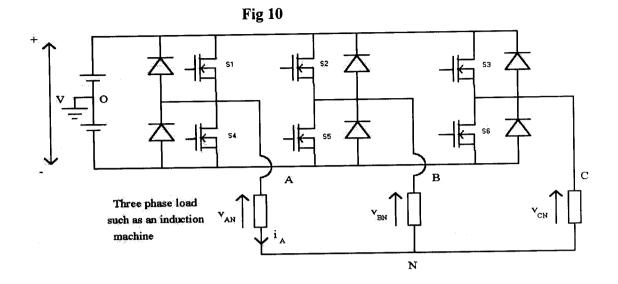
Fig 9

#### 6.3 Three phase inverters:

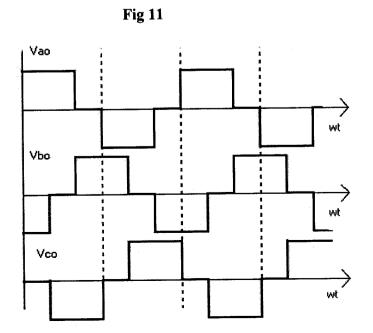
Three phase inverters are more common in industrial applications due to their superior power capabilities. There are usually six power switches used in these inverters. There are two ways in which a 3 phase ac output can be produced from this inverter,

- (i) 180° Conduction of power elements
- (ii) 120° Conduction of power elements

In the first case three power elements are ON at any instant and they each conduct for half a cycle. In the second case only two power elements are ON at any instant and they conduct for one third of the cycle. In both cases the gating signals of the power elements' are delayed by 60° mutually with respect to one another. The following diagram shows the 3 phase inverter:



In 120° degree conduction mode two power elements are ON at any instant of time, remaining ON for one thirds of a cycle and separated from each other by 60°. The gating signals follow a similar pattern, the sequence for the schematic shown above:(1,5),(1,6),(6,2),(2,4),(4,3),(3,5) before the sequence repeats again. The output of the inverter for the above operation is as shown:



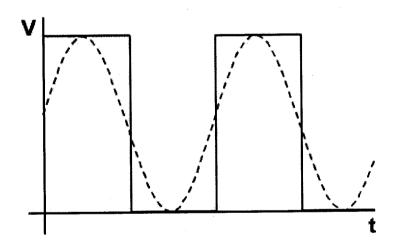
In both the inverters mentioned above the output is a coarse approximation of a sine wave with a large amount of harmonics still present. This can be avoided by the use of Pulse Width Modulation(PWM) wherein a series of pulses are fed as the gating signals instead of a single pulse per element per cycle. On filtering the output the output shown above using an L-C filter a smooth sinusoidal output can be obtained.



#### 7.1 Overview:

In previous methods all the devices were switched with the same frequency of singular pulses, this provides an output that is a poor approximation of the sine wave. Pwm uses a train of pulses of varying duty cycle to control the output of the inverter to a close sine wave approximation. The following illustration shows the concept:

Fig 12



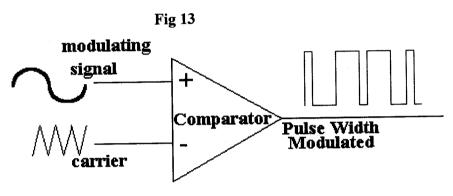
- ---- Actual squarewave output
- --- Sinewave that is being approximated

There are many ways of generating a pwm output including

- Single pulse width modulation
- Multiple pulse width modulation
- Sinusoidal pulse width modulation
- Modified pulse width modulation
- Phase displacement control

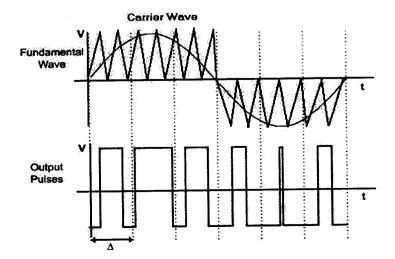
#### 7.2 Sinusoidal Pulse Width Modulation:

Although these are different ways of generating a pwm wave they differ only in the carrier circuit used fot modulating the input signal. The following illustration shows the principle behind generating these pwm waves.



Since the inverter must produce an output that is a close approximation of a sine wave the pwm signals used in an inverter must follow a sinusoidal modulation. The following illustration shows the pwm output after a sinusoidal modulation:

Fig 14



As shown in the diagram, the gating pulses to the MOSFETs are varying the duty cycle of the MOSFET according to a sinusoidal wave. Thus a close approximation to a sie wave can be obtained as an output. After sufficient filtering a perfect sinusoidal wave can be obtained.



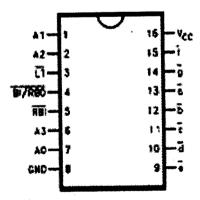
The frequency set by the user is displayed as asset value using the display segment. The segment consists of standard seven segment displays and BCD to seven segment decoder/driver IC(74LS47).

The BCD to seven segment decoder/driver IC is primary controller of the sdisplay, has the following key features:

- ♦ The DM74LS47 accepts four lines of BCD (8421) input data, generates their complements internally and decodes the data with seven AND/OR gates having open-collector outputs to drive indicator segments directly.
- Auxiliary inputs provided for lamp test, blanking, cascadable zero suppression.

The illustration below shows the pin diagram and the pin description:

**Fig 15** 



## **Pin Descriptions**

Pin Names	Description
A0-A3	BCD Inputs
<b>रा</b> धा	Ripple Blanking Input (Active LOW)
T	Lamp Test Input (Active LOW)
EV/REO	Blanking Irout (Active LOW) or
	Ripple Blanking Output (Active LOW)
ā-g	Segment Outputs (Active LOW) (Note 1)

A total of three BCD to seven segment decoder/driver Ics have been used in the display segment and the inputs to the drivers are obtained from separate microcontroller ports. The following table shows the truth table of the driver:

**Fig 16** 

Or Or	Inputs							Outputs						
Function	LT	RBI	A3	A2	A1	AĐ	BI/RBO	ā	b	Ç	d	ē	Ť	g
0	H	Н	L	L	L	L	Н	L	L	L	L	L	L	Н
1	Н	х	L	L	L	. Н	н	Н	L	L	Н	Н	Н	Н
2	Н	X	L	L	Н	L	Н	L	L	Н	L	L	Н	L
3	н	x	L	L	Н	Н	н	L	L	L	L	Н	Н	L
4	н	x	L	н	L	L	н	Н	L	L	н	н	L	L
5	н	x	L	Н	L	Н	н	L	Н	L	L	Н	L	L
6	н	Х	L	Н	Н	L	Н	Н	н	L	L	L	L	L
7	Н	X	L	Н	н	Н	H	L	L	L	н	Н	Н	Н
8	н	x	н	L	L	L	Н	L	L	L	L	L	L	L
9	н	×	н	L	L	н	н	L	L	L	Н	н	L	L
10	Н	х	н	L	Н	L	н	Н	Н	Н	Ł	L	Н	L
11	н	X	н	L	Н	н	i H	Н	H	L	L	Н	Н	L
12	Н	X	Н	Н	Ļ	L	н	н	L	Н	H	Н	L	L
13	н	x	H-	Н	L	Н	Н	L	Н	Н	L	Н	L	L
14	н	x	Н	н	н	L	н	н	н	н	L	L	L	ι
15	н	X	Н.	Н	Н	н	н	Н	Н	Н	Н	н	Н	ŧ
ष्ठा	x	х	x	X	X	X	L	н	Н	Н	Н	Н	н	ł
RBI	н	L	L	L	L	L	į L	н	Н	Н	Н	Н	Н	ŀ
ĹΤ	lь	l x	l x	Х	X	X	н	L	L	L	L	L	L	l



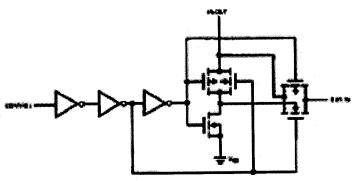
The microcontroller needs to protected or isolated from the power element or the inverter segment. Furthermore the microcontroller provides a PWM output only in one of its output ports and in particular only one pin. To effectively isolate and also efficiently switch multiple power elements simultaneously, the switching and isolation segment is essential. This segment consists of two basic components:

- (i) Digital/Analog switches
- (ii) Optical Isolators

### 9.1 Digital/Analog switches:

The switching of multiple power elements is achieved by the usage of the Quad Bilateral Switch provided in the CD4066 integrated circuit. The afore mentioned IC has the following internal schematic:

Fig 17
Schematic Diagram



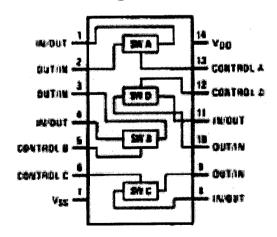
The typical features of this analog/digital switch are:

- High noise immunity.
- Wide range of digital and analog switching.
- ON resistance flat over peak to peak signal range.
- □ High ON/OFF output voltage ratio.
- Extremely high control input impedance.
- Frequency range of over 40 MHz.
- High degree linearity.

The internal connection diagram of the analog/digital switch package is shown below:

Fig 17

Connection Diagram



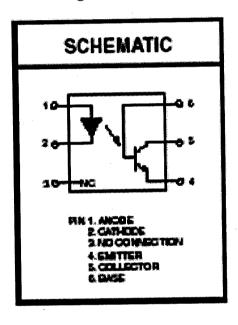
The typical applications include signal gating, chopper, commutating switch, multiplexing etc.

#### 9.2 Optical Isolators:

The optoisolators act as buffers between the microcontroller and the high voltage side thus shielding the microcontroller from damage.

The optoisolators used employ light emitting diodes in one side and photo transistors on the other side to effectively act as a buffer between two different voltage levels. The schematic used is as shown:

**Fig 18** 

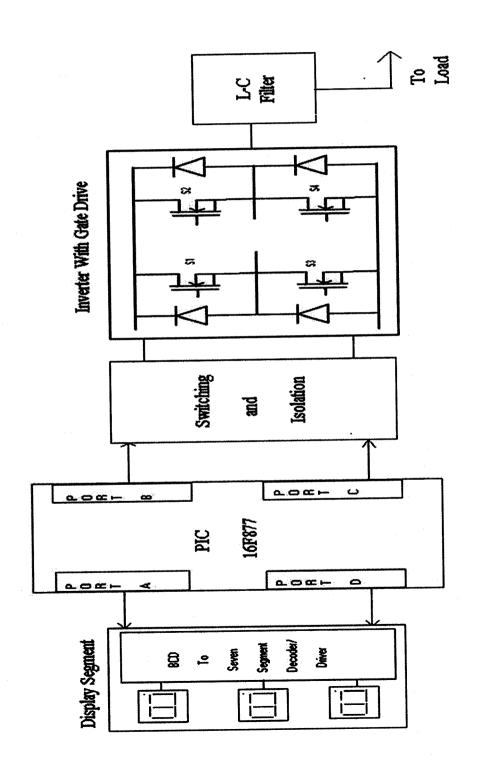


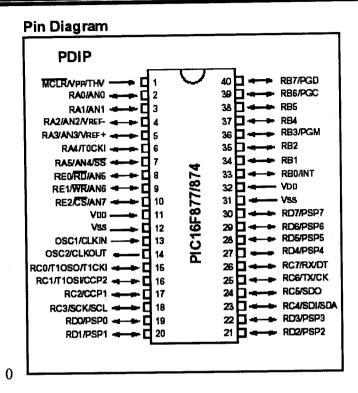
Chapter10 – Control Segment

The control segment primarily consists of the PIC 16F877 microcontroller and its related components. The microcontroller is the heart of the whole project, directing various activities simultaneously. The activities of the microcontroller include:

- ❖ Generating PWM output for various sine frequencies specified by the user.
- Scanning for user input from interrupt sources.
- Constantly updating PWM duty cycle and period.
- Converting analog inputs into digital data for further processing and display.
- Monitoring and discriminating interrupts and analog inputs.

The following illustration shows the functional blocks of the control segment along with the peripheral segments:





**Microcontroller Core Features:** 

- High-performance RISC CPU
- Only 35 single word instructions to learn
- All single cycle instructions except for program branches which are two cycle
- Operating speed: DC 20 MHz clock input
- DC 200 ns instruction cycle
- Up to 8K x 14 words of FLASH Program Memory,

Up to 368 x 8 bytes of Data Memory (RAM)

Up to 256 x 8 bytes of EEPROM data memory

- Interrupt capability (up to 14 sources)
- Direct, indirect and relative addressing modes

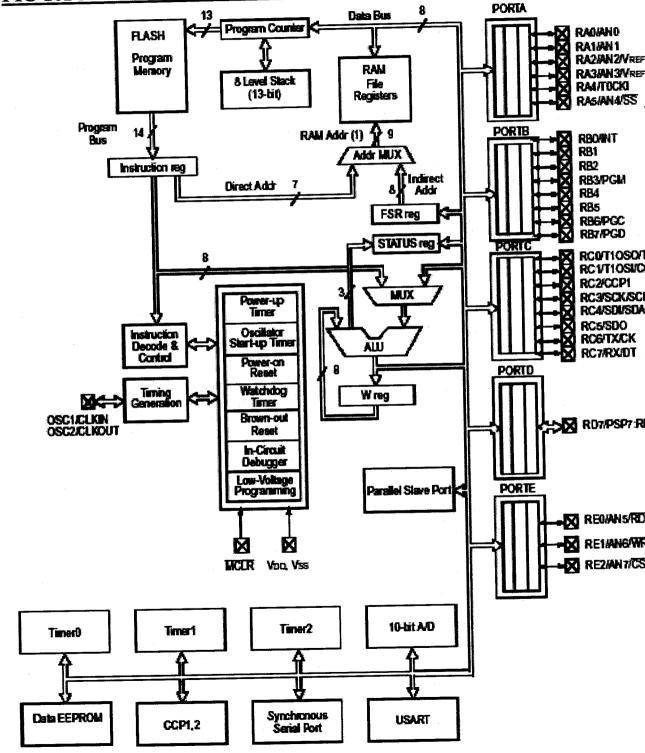
- Power-on Reset (POR)
- Power-up Timer (PWRT)
- Watchdog Timer (WDT) with its own on-chip RC oscillator for reliable operation
- Fully static design
- In-Circuit Serial Programming ☐ (ICSP) via two pins
- Processor read/write access to program memory
- Wide operating voltage range: 2.0V to 5.5V
- Commercial and Industrial temperature ranges
- Low-power consumption:
- < 2 mA typical @ 5V, 4 MHz
- 20 □ A typical @ 3V, 32 kHz
- -<1  $\square$  A typical standby current

#### **Peripheral Features:**

- Timer0: 8-bit timer/counter with 8-bit prescaler
- Timer1: 16-bit timer/counter with prescaler, can be incremented during sleep via external crystal/clock
- Timer2: 8-bit timer/counter with 8-bit period register, prescaler and postscaler
- Two Capture, Compare, PWM modules
- Capture is 16-bit, max. resolution is 12.5 ns
- Compare is 16-bit, max. resolution is 200 ns
- PWM max. resolution is 10-bit

- 10-bit multi-channel Analog-to-Digital converter
- Synchronous Serial Port (SSP) with SPI□(Master Mode) and I2Ç□ (Master/Slave)
- Universal Synchronous Asynchronous Receiver Transmitter (USART/SCI) with 9-bit address detection
- Parallel Slave Port (PSP) 8-bits wide, with external RD, WR and CS controls (40/44-pin only)
- Brown-out detection circuitry for Brown-out Reset (BOR)

# PIC 16F877 ARCHITECTURE:

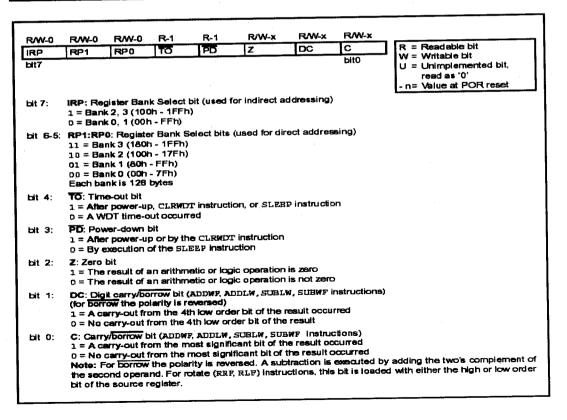


# **Program Memory Organization:**

The PIC16F87X devices have a 13-bit program countercapable of addressing an 8K x 14 program memory space. The PIC16F877/876 devices have 8K x 14words of FLASH program memory and the PIC16F873/874 devices have 4K x 14. Accessing a location above the physically implemented address will cause a wrap around. The reset vector is at 0000h and the interrupt vector is at 0004h.

## **Special Function Registers:**

## **STATUS Register:**



## **INTCON Register:**

R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	RW-0	R/W-0	R/W-x	D - Beedeblo hit	
GIE	PEE	TOIE	INTE	RBIE	TOIF	INTF	RBIF	R = Readable bit W = Writable bit	
bit7							bit0	U = Unimplemented bit, read as '0' - n= Value at POR reset	
bit 7:	1 = Enat 0 = Disa	oles all un bies all in	•	nterrupts					
bit 6:	bit 6: PEIE: Peripheral Interrupt Enable bit  1 = Enables all un-masked peripheral interrupts 0 = Disables all peripheral interrupts								
bit 5:	5: TOLE: TMR0 Overflow Interrupt Enable bit  1 = Enables the TMR0 interrupt  0 = Disables the TMR0 interrupt								
bit 4:									
bit 3:	RBIE: RB Port Change Interrupt Enable bit  1 = Enables the RB port change interrupt  0 = Disables the RB port change interrupt								
bit 2:	2: T01F: TMR0 Overflow Interrupt Flag bit  1 = TMR0 register has overflowed (must be cleared in software)  0 = TMR0 register did not overflow								
bit 1:	1: INTF: RB0/INT External Interrupt Flag bit 1 = The RB0/INT external interrupt occurred (must be cleared in software) 0 = The RB0/INT external interrupt did not occur								
bit 0:	1 = At le	ast one o	nange Inte of the RB7 RB7:RB4 p	RB4 pins	bit changed s changed st	state (must ate	be cleared	in software)	
				-					

## I/O Ports:

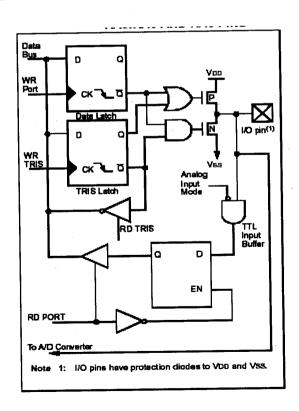
Most of the pins for I/O ports are multiplexed with an alternate function for the peripheral features on the device. In general, when a peripheral is enabled, that pin may not be used as a general purpose I/O pin.

# **PORTA and the TRISA Register:**

PORTA is a 6-bit wide bi-directional port. The corresponding data direction register is TRISA. Setting a TRISA bit (=1) will make the

corresponding PORTA pin an input (i.e., put the corresponding output driver in a hi-impedance mode). Clearing a TRISA bit (=0) will make the corresponding PORTA pin an output (i.e., put the contents of the output latch on the selected pin). Reading the PORTA register reads the status of the pins, whereas writing to it will write to the port latch. All write operations are read-modify-write operations. Therefore, a write to a port implies that the port pins are read, the value is modified and then written to the port data latch.

# **Structure Of I/O Port Pins:**



# **PORTB and the TRISB Register:**

PORTB is an 8-bit wide, bi-directional port. The corresponding data direction register is TRISB. Setting a TRISB bit (=1) will make the corresponding PORTB pin an input (i.e., put the corresponding output driver in a hi-impedance mode). Clearing a TRISB bit (=0) will make the corresponding PORTB pin an output (i.e., put the contents of the output latch on the selected pin). Three pins of PORTB are multiplexed with the Low Voltage Programming function; RB3/PGM, RB6/PGC and RB7/PGD. Each of the PORTB pins has a weak internal pull-up. A single control bit can turn on all the pull-ups. This is performed by clearing bit RBPU (OPTION\_REG<7>).

Four of PORTB's pins, RB7:RB4, have an interrupt on change feature. Only pins configured as inputs can cause this interrupt to occur (i.e. any RB7:RB4 pin configured as an output is excluded from the interrupt on change comparison).

# **PORTC and the TRISC Register**

PORTC is an 8-bit wide, bi-directional port. The corresponding data direction register is TRISC. Setting a TRISC bit (=1) will make the corresponding PORTC pin an input (i.e., put the corresponding output driver in a hi-impedance mode). Clearing a TRISC bit (=0) will make the corresponding PORTC pin an output (i.e., put the contents of the output

latch on the selected pin). PORTC is multiplexed with several peripheral functions. PORTC pins have Schmitt Trigger input buffers. When enabling peripheral functions, care should be taken in defining TRIS bits for each PORTC pin. Some peripherals override the TRIS bit to make a pin an output, while other peripherals override the TRIS bit to make a pin an input.

## **TIMER2 MODULE**

Timer2 is an 8-bit timer with a prescaler and a postscaler. It can be used as the PWM time-base for the PWM mode of the CCP module(s). The TMR2 register is readable and writable, and is cleared on any device reset. The input clock (FOSC/4) has a prescale option of 1:1, 1:4 or 1:16, selected by control bits T2CKPS1:T2CKPS0 (T2CON<1:0>). The Timer2 module has an 8-bit period register PR2. Timer2 increments from 00h until it matches PR2 and then resets to 00h on the next increment cycle. PR2 is a readable and writable register. The PR2 register is initialized to FFh upon reset. The match output of TMR2 goes through a 4-bit postscaler (which gives a 1:1 to 1:16 scaling inclusive) to generate a TMR2 interrupt (latched in flag bit TMR2IF, (PIR1<1>)). Timer2 can be shut off by clearing control bit TMR2ON (T2CON<2>) to minimize power consumption.

# **Timer2 Prescaler and Postscaler**

The prescaler and postscaler counters are cleared when any of the following occurs:

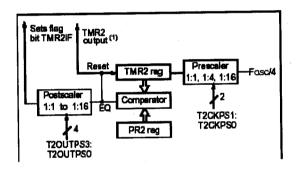
- a write to the TMR2 register
- a write to the T2CON register

• any device reset (POR, MCLR reset, WDT reset or BOR)
TMR2 is not cleared when T2CON is written.

## **Output of TMR2**

The output of TMR2 (before the postscaler) is fed to the SSPort module, which optionally uses it to generate shift clock.

### **TIMER 2 BLOCK DIAGRAM:**



## **T2CON REGISTER:**

```
R/W-0
                                                    R/W-0
                                                                RAW-0
                                                                          R/W-0
                               R/W-0
  U-0
         TOUTPS3 TOUTPS2 TOUTPS1 TOUTPS0 TMR2ON T2CKPS1 T2CKPS0
                                                                                        = Readable bit
                                                                                        = Writable bit
                                                                                        = Unimplemented bit,
                                                                                          read as '0'
                                                                                      n = Value at POR reset
         Unimplemented: Read as '0'
bit 7:
         TOUTPS3:TOUTPS0: Timer2 Output Postscale Select bits
bit 6-3:
         ogog = 1:1 Postscale
         ogga = 1:2 Postscale
         0010 = 1:3 Postscale
         1111 = 1:16 Postscale
bit 2:
         TMR2ON: Timer2 On bit
         1 = Timer2 is on
         a = Timer2 is off
         T2CKPS1:T2CKPS0: Timer2 Clock Prescale Select bits
bit 1-0:
         oc = Prescaler is 1
         on = Prescaler is 4
          1x = Prescaler is 16
```

## CAPTURE/COMPARE/PWM MODULES

Each Capture/Compare/PWM (CCP) module contains a 16-bit register which can operate as a:

- 16-bit Capture register
- 16-bit Compare register
- PWM master/slave Duty Cycle register

Both the CCP1 and CCP2 modules are identical in operation, with the exception being the operation of the special event trigger.

#### **CCP1 Module:**

Capture/Compare/PWM Register1 (CCPR1) is comprised of two 8-bit registers: CCPR1L (low byte) and CCPR1H (high byte). The CCP1CON register controls the operation of CCP1. The special event trigger is generated by a compare match and will reset Timer1.

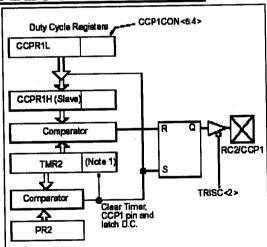
#### **CCP2 Module:**

Capture/Compare/PWM Register1 (CCPR2) is comprised of two 8-bit registers: CCPR2L (low byte) and CCPR2H (high byte). The CCP2CON register controls the operation of CCP2. The special event trigger is generated by a compare match and will reset Timer1 and start an A/D conversion (if the A/D module is enabled).

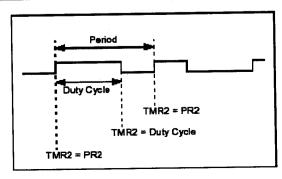
#### PWM Mode (PWM)

In pulse width modulation mode, the CCPx pin produces up to a 10-bit resolution PWM output. Since the CCP1 pin is multiplexed with the PORTC data latch, the TRISC<2> bit must be cleared to make the CCP1 pin an output.

# **PWM MODULE BLOCK DIAGRAM:**



# **SAMPLE PWM WAVE FORM:**



#### **PWM PERIOD:**

The PWM period is specified by writing to the PR2 register. The PWM period can be calculated using the following formula:

PWM period = [(PR2) + 1] • 4 • TOSC • (TMR2 prescale value)

PWM frequency is defined as 1 / [PWM period]. When TMR2 is equal to PR2, the following three events occur on the next increment cycle:

- TMR2 is cleared
- The CCP1 pin is set (exception: if PWM duty cycle = 0%, the CCP1 pin will not be set)
- The PWM duty cycle is latched from CCPR1L into CCPR1H

# **PWM DUTY CYCLE:**

The PWM duty cycle is specified by writing to the CCPR1L register and to the CCP1CON<5:4> bits. Up to 10-bit resolution is available. The CCPR1L contains the eight MSbs and the CCP1CON<5:4> contains the two LSbs. This 10-bit value is represented by CCPR1L:CCP1CON<5:4>. The following equation is used to calculate the PWM duty cycle in time:

PWM duty cycle =

(CCPR1L:CCP1CON<5:4>) • Tosc • (TMR2 prescale value)

CCPR1L and CCP1CON<5:4> can be written to at any time, but the duty cycle value is not latched into CCPR1H until after a match between PR2 and TMR2 occurs (i.e., the period is complete). In PWM mode, CCPR1H is a read-only register.

Maximum PWM resolution (bits) for a given PWM frequency:

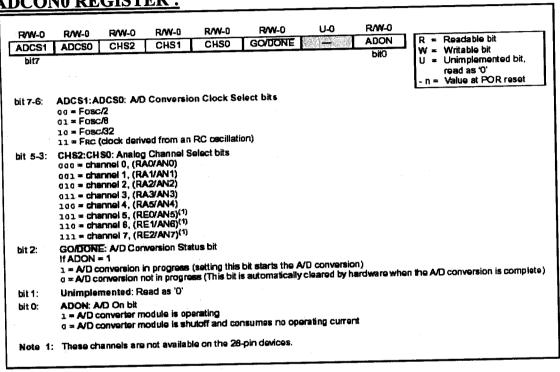
$$Resolution = \frac{\log(\frac{FOSC}{FPWM})}{\log(2)} bits$$

# ANALOG-TO-DIGITAL CONVERTER (A/D) MODULE:

The Analog-to-Digital (A/D) Converter module has five inputs for the 28-pin devices and eight for the other devices. The analog input charges a sample and hold capacitor. The output of the sample and hold capacitor is the input into the converter. The converter then generates a digital result of this analog level via successive approximation. The A/D conversion of the analog input signal results in a corresponding 10-bit digital number. The A/D module has high and low voltage reference input that is software selectable to some combination of VDD, VSS, RA2 or RA3. The A/D converter has a unique feature of being able to operate while the device is in SLEEP mode. To operate in sleep, the A/D clock must be derived from the A/D's internal RC oscillator.

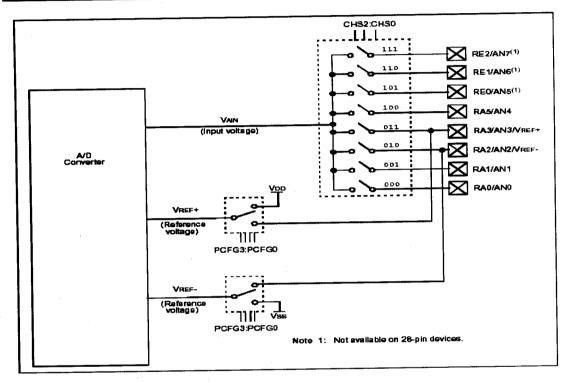
The ADCON0 register, shown in Register, controls the operation of the A/D module. The ADCON1 register, shown in Register 11-2, configures the functions of the port pins. The port pins can be configured as analog inputs (RA3 can also be the voltage reference) or as digital I/O.

**ADCONO REGISTER:** 



The ADRESH:ADRESL registers contain the 10-bit result of the A/D conversion. When the A/D conversion is complete, the result is loaded into this A/D result register pair, the GO/DONE bit (ADCON0<2>) is cleared and the A/D interrupt flag bit ADIF is set. After the A/D module has been configured as desired, the selected channel must be acquired before the conversion is started. The analog input channels must have their corresponding TRIS bits selected as inputs. After this acquisition time has elapsed, the A/D conversion can be started.

# A/D Converter Block Diagram:



## A/D Acquisition Requirements

For the A/D converter to meet its specified accuracy, the charge holding capacitor (CHOLD) must be allowed to fully charge to the input channel voltage level. The analog input model is shown in Figure .

To calculate the minimum acquisition time, the following equation is used.

```
Tacq = Amplifier Settling Time +
Hold Capacitor Charging Time +
Temperature Coefficient

= TAMP + TC + TCOFF
= 2\muS + TC + [(Temperature -25°C)(0.05\muS/°C)]

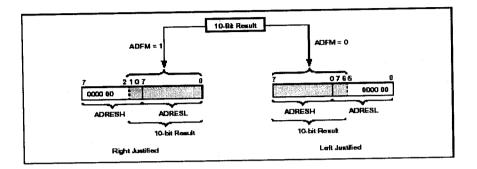
TC = CHOLD (RIC + RSS + RS) In(1/2047)
= -120pF (1k\Omega + 7k\Omega + 10k\Omega) In(0.0004885)
= 16.47\muS

Tacq = 2\muS + 16.47\muS + [(50°C -25×C)(0.05\muS/×C)
= 19.72\muS
```

A/D CONVERTER MODEL: **┼ ∨**⊤ = 0.6∨ Ric s 1k SS Rss CHOLD = DAC capacitance = 120 pF EAKAGE 500 IIA Vr = 0.6Vi= input capacitance Legend CPIN threshold voltage
 leakage current at the pin due to various junctions = interconnect resistance Ric SS = sampling switch = sample/noid capacitance (from DAC) CHOLD Sampling Switch (kΩ)

## A/D RESULT REGISTERS

The ADRESH:ADRESL register pair is the location where the 10-bit A/D result is loaded at the completion of the A/D conversion. This register pair is 16-bits wide. The A/D module gives the flexibility to left or right justify the 10-bit result in the 16-bit result register. The A/D Format Select bit (ADFM) controls this justification. The figure shown below shows the operation of the A/D result justification. The extra bits are loaded with '0's'. When an A/D result will not overwrite these locations (A/D disable), these registers may be used as two general purpose 8-bit registers.



The software used in the project has been divided into two major modules,

- (i) A/D conversion, display and interrupt service module.
- (ii) PWM duty cycle and period update module.

The A/D conversion and interrupt service module constantly scans for new user inputs and converts them to BCD values for display. It also services the various user interrupts and internal software interrupts.

The PWM module updates the duty cycles of the gating signals by using a sine wave lookup table stored by the programmer, it also updates the PWM period by accepting new frequencies from the user.

The following pages show the source codes used and their respective control flow.

# 11.1 Analog to Digital conversion, interrupt service and display routine:

# Source code:

;=====A/D Conversion with display routine=====
list p=16f877
include <p16f877.inc></p16f877.inc>
;====sfr addresses initialisation=====
status equ 03h
portb equ 06h
trisb equ 86h
portd equ 08h
trisd equ 88h
intcon equ 0bh
pir1 equ 0ch
piel equ 8ch
adresh equ 1eh
adcon0 equ 1fh
adcon1 equ 9fh
porte equ 07h
trisc equ 87h
porta equ 05h
trisa equ 85h
;====Define vector locations=====
org 0x000

goto start		
org 0x004		
goto introutine		
;=====Defi	ne user variables=====	
cblock 20h		
index		
var		
digit0		
digit1		
digit2		
temp1		
temp2		
temp3		
endc		
;=====Inte	errupt service routine=====	
introutine		
bcf status,5	;clear interrupt flag bits	
btfsc pir1,6		
call adover		
movf portb,0		
clrf intcon		
bsf intcon,7		
bsf intcon,3		
goto adstart		
;=====ma	in routine======	
adinitialise	;initialize a/d converter	

```
clrf pie1
  bsf pie1,6
  movlw B'11110000'
  movwf trisa
  clrf trisc
   movlw B'00000000'
   movwf trisc
   movlw B'00001110'
   movwf adcon1
   bcf status,5
   bcf pir1,6
   clrf portc
   movlw B'00000000'
   movwf adcon0
   clrf adresh
                                   ;initialize user variables
   clrf var
   clrf digit0
    clrf digit1
    clrf digit2
return
                              ;start a/d conversion
adstart
    bsf adcon0,0
    call adcdelay
    bsf adcon0,2
```

bsf status,5

call adcdelay

```
;acquisition delay for a/d conversion
adcdelay
      loop1
      movlw d'1'
      movwf temp1
  loop2
      movlw d'30'
      movwf temp2
  loop3
      clrwdt
      decfsz temp2,1
      goto loop3
      decfsz temp1,1
      goto loop2
       return
 adover
       bsf pie1,6
       bsf intcon,7
       bcf pir1,6
       movf adresh,0
       movwf var
                                ;binary to bcd conversion
   bin2bcd
   loophun
       movlw .100
       subwf var,w
```

```
btfss status,0
   goto huover
   incf digit2,1
   movwf var
    goto loophun
huover
    movlw .0
loopten
    movlw.10
    subwf var,w
    btfss status,0
    goto teover
    incf digit1,1
    movwf var
    goto loopten
 teover
    movf var,0
    movwf digit0
                                    ;display procedure
     swapf digit0,1
     movf digit0,0
     movwf porta
     swapf digit2,1
     movf digit2,0
     addwf digit1,0
     movwf portd
```

goto wait

```
start
```

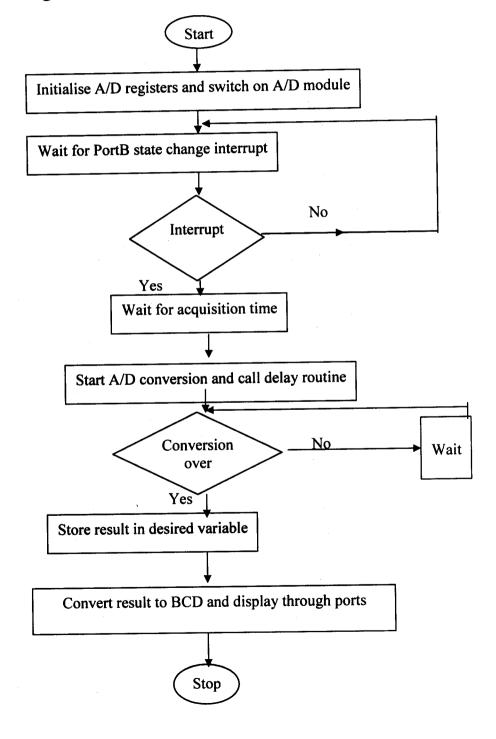
end

#### ;program starts

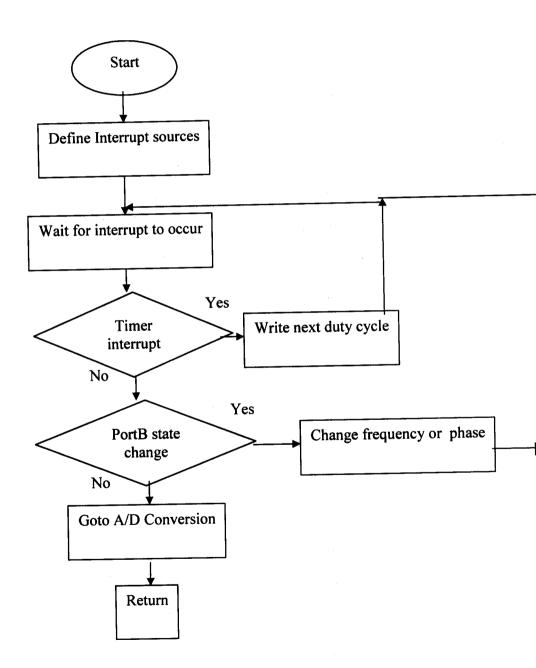
call adinitialise clrf status clrf portb clrf intcon bsf intcon,7 bsf intcon,3 clrf portd bsf status,5 clrf trisb movlw b'11110000' movwf trisb movlw b'00000000' movwf trisd movlw b'11111111' movwf portd wait goto wait

#### Flowcharts:

# 11.2 Analog to Digital conversion:



# **Interrupt Service:**



# 11.3 PWM Duty cycle and period update routine:

**Source Code:** 

ccprlh equ 16h

;====pwm routine==== list p=16f877include <p16f877.inc> intcon equ 0bh adresh equ 1eh adcon0 equ 1fh adcon1 equ 9fh portd equ 08h trisd equ 88h portb equ 06h trisb equ 86h portc equ 07h trisc equ 87h status equ 03h tmr2 equ 11h t2con equ 12h pr2 equ 92h pir1 equ 0ch ccprll equ 15h

```
ccp1con equ 17h
pcl equ 02h
piel equ 8ch
;----user variables definition----
cblock 20h
index
endc
:----define vector locations
org 0x000
goto start
org 0x004
goto introutine
;=====interrupt service routine=====
 introutine
                     ;clear interrupt flag bits
     bcf status,5
     bcf pir1,1
     bsf intcon,7
     bsf status,5
     bsf pie1,2
     goto dcroutine
          ====main routine===
 start
     clrf portb
     clrf portc
     clrf status
                      ;set up status reg
     clrf tmr2
```

clrf pirl bsf status,5 ;clear pwm period clrf pr2 clrf trisc clrf trisb clrf pie1 bsf pie1,1 movlw .255 ;setup pwm period movwf pr2 bcf status,5 bsf intcon,7 bsf intcon,6 ;clear pwm control register clrf ccplcon ;clear pwm duty cycle register clrf ccpr11 ;configure ccp register bsf ccplcon,2 bsf ccp1con,3 movlw .0 movwf ccpr11 repeat bsf portb,4 bsf portb,5 bcf portb,1 bcf portb,3 movlw .3 movwf index ;switch timer2 on bsf t2con,2

clrf t2con

```
goto pinchange
      ____timer poll___
                                  ;duty cycle routine
dcroutine
    bcf pir1,1
    bcf t2con,2
    clrf tmr2
                                   ;call duty cycle lookup table
     call sinetable
     incf index,1
     movwf ccpr11
     bsf t2con,2
   ____port pin change===
pinchange
t2polli
     btfsc portc,2
      goto t2polli
     bcf portb,4
     bcf portb,5
     nop nop nop
     nop nop nop
     bsf portb,1
     bsf portb,2
 wait
      goto wait
             _____look up table=====
sinetable
      movf pcl,0
```

addwf index,0

movwf pcl	
retlw .128	;0 degree, 2.5 volts
retlw .148	
retlw .167	
retlw .185	
retlw .200	
retlw .213	
retlw .222	
retlw .228	
retlw .230	;90 degree, 4.5 volts
retlw .228	
retlw .222	
retlw .213	
retlw .200	
retlw .185	
retlw .167	
retlw .148	
retlw .128	;180 degree, 2.5 volts
retlw .108	
retlw .89	
retlw .71	
retlw .56	
retlw .43	
retlw .34	
retlw .28	
retlw .26	;270 degree, 0.5 volts
retlw .28	

retlw .34

retlw .43

retlw .56

retlw .71

retlw .89

retlw .108

movlw .0

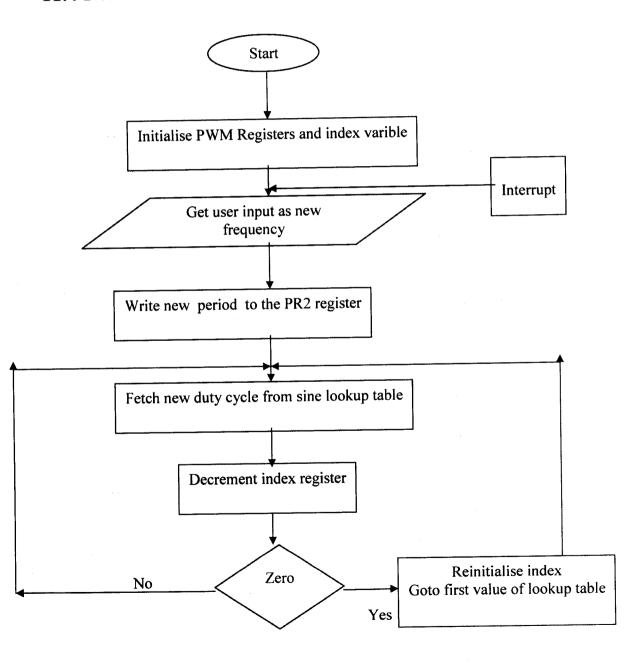
movwf index

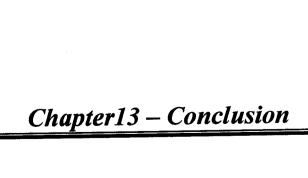
goto repeat

end

#### Flowchart:

#### 11.4 PWM Routine:





The emerging trends in high frequency power would certainly prove to be beneficial for the consumer. The cost and size of almost all electrical applications would be reduced. Our project can generate frequencies of up to 255 Hz. with the current hardware. With simple hardware modifications frequencies of 500 Hz or more can be generated.

The microcontroller used in the project enables us to generate 'harmonics free' outputs that can be used for sensitive and common applications. The project can be further developed to generate high voltage ac with improved hardware. The prospect of using high frequency power alone in the future provides the basis for further development of the project.

# References and Bibliography

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- ♦ A 500 Hz Power System -Power converters, by I.Takahashi and G.J.Su- IEEE Transactions on Industrial Applications 1999.]
- ♦ Power Electronics, circuits, devices and applications by Muhammed.H.Rashid, 12<sup>th</sup> editon − 2000
- ♦ Power Electronics by Dr.P.S.Bhimbra, 5<sup>th</sup> edition- 2001
- ◆ Power Electronics and motor Control by W.Shepherd and D.T.W.Liang, 2<sup>nd</sup> edition-2001
- ♦ WWW.irf.com
- ♦ <u>WWW.microchip.com</u>

# Special Function Rgisters(SFR) :

#### **ADCON1 Register:**

U-O	- 11-0	RAW-D	U-Q	RAW-0	R/W-0	RAW-0	RAW-0
ADFM	-		-	PCFG3	PCFG2	PCFG1	PCFG0
547							bitO

R = Readable bit W = Wrtable bit

U = Unimplemented bit, read as '0' n = Value at POR reset

ADFM: A/D Result format select bit 7:

2 = Right Justified. 8 most significant bits of ADRESH are read as '0'. 0 = Left Justified. 8 least significant bits of ADRESL are read as '0'.

bit 6-4: Unimplemented: Read as '0'

bit 3-0: PCFG3:PCFG0: A/B Port Configuration Control bits

PCFG3: PCFG0	AN7 <sup>(1)</sup> RE2	ANG <sup>(1)</sup> RE1	ANS <sup>(1)</sup> RED	AN4 RAS	AN3 RA3	AN2 RA2	AN1 RA1	ANO RAD	VALEF+	VREF-	CHAN / Refs(P)
8000	A	A	Α.		٨	A	A	Α	Voo	Vas	640
0001	A	Α	A	A	VREF+	A	Α	Α	RA3	Vss	7/1
8010	D	D	<u> </u>	A	Α	Α	Α	Α	Vap	Vss	5/0
	-	<u> </u>	<u> </u>	A	VREF+	A	A	A	RA3	Vas	4/1
0011	0	0	6	D	Α.	D	A	Α	Voo	Vas	3/0
81.00	<u> </u>	0	-	0	VREF+	D	A	A	RAS	Vas	2/1
0101	0			H	D	D	В	0	Voo	VSS	מעם
DLLX	0	0	D		VREF+	VREF-	A	Ā	RA3	RA2	6/2
1000	A	A_	. A	<u> </u>		A	A	A	Voo	VSS	6/0
1001	D	D	A .	<u>^</u>	A A		A	A	RA3	Vas	5/1
1010	0_	D	Α		VREF+	Λ.				RA2	4/2
1011	D	0	Α	A	VREF+	VREF-	A	A	RA3		-
1100	0	0	D	Α.	VREF+	VREF-	Α	A	RA3	RA2	3/2
1101	D	D	ם	D	VREF+	VREF-	A	A.	RA3	RA2	2/2
1110	D	D	р	п	D	D	D	A	VDD	Vas	1/0
1111	1 5	D	D	В	VREF+	VREF-	D	Α	RA3	RA2	1/2

A = Analog input

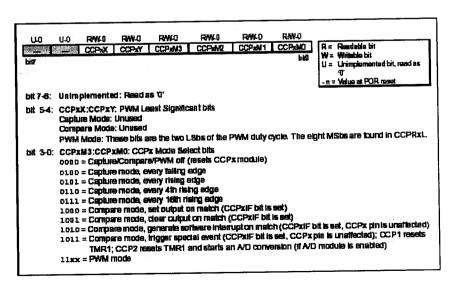
D = Digital FO

Note 1: These channels are not available on the 28-pin devices.
2: This column indicates the number of analog channels available as A/D inputs and the numer of analog channels. used as voltage reference inputs.

#### **Interaction between CCP modules:**

CCPx Mode	CCPy Mode	Interaction
Capture	Capture	Same TMR1 time-base.
Capture	Compare	The compare should be configured for the special event trigger, which clears TMR1.
Compare	Compare	The compare(s) should be configured for the special event trigger, which clears TMR1.
PWM	PWM	The PWMs will have the same frequency and update rate (TMR2 interrupt).
PWM	Capture	None.
PWM	Compare	None.

#### **CCP1CON/CCP2CON Registers:**



# Registers associated with PWM operation:

Address	Namo	Bit 7	9it C	Bits	Bit4	Bit 3	Bit 2	Efit 1	Bit 0	Value PO BC	R,	Velu all o	ther
091,881, 1091,1891	INTERN	GIE	PBE	TOE	INTE	HEE:	TOF	INTE	HEF	0000	BOOK:	9000	0001
OCh	PIR1	ecoldy	ADIF	RCF	TREF	88AF	CCFIF	TMRZIF	TARRE	0000	0000	8080	0000
ODh	PIR2					-		-	CCP2IF		B		0
8Ch	PIE1	Consider	ADE	cos	1905	TO SE	ESSIE :	TWRZE	THREE	8080	0000	0000	0000
		100000		200000000000000000000000000000000000000					CCP2E		0		0
8Dh	PIEZ .		0 0							1111	1111	1111	1111
B7h	TRISC			ion Regists	lT .					6000	0.556	9000	8080
116	TMF2	Timer2 n	per selubar	istor .								1111	
92h	PR2	Timer2 n	nodula s par	ricid regists	r							_	
12h	TZCON	-	TOUTPES	TOUTPS	TOUTPS	TOUTPSO	TIMESON	TECKPS	T2CKPS0		0000		0000
15h	CCPRIL	Captre	Comparal	WM regists	r1 (LSB)							An an	
16h	CCPRIH	Cautro	Compare/F	WM agists	×1 (MSE)					XXXX	XXXX	uuuu	num
17h	CCPICON			CCPIX		CCP1M3	CCP1M2	CCPIMI	CCPIMO	00	0000	80	0000
12h	CCPR2L		Communic	WM regists	×2 (LSB)		<u> </u>			XXXX	XXXX	uunu	num
										XXX	XXXX	nunu	num
1Ch	CCPR2H	Cabro		WM region		1	Language	CCP2M1	ACCURATE OF	80	BAAB	00	0000
1Dh	CEPZCON	-	-	CCP2X	CCPZY	CCCb.5M3	CCP2M2	LUPZMI	COLLEGE STATE	00	2000	[ W.	~~~

# Registers associated with Analog/Digital conversion:

Addr	Name	BR7	8 K 6	BR 5	Bit 4	B# 3	BIt 2	Bit 1	Bit 0	POR, BOR	MCLR, WDT
CET1	INTCON	GIE	PEE	100 TT 100	-MIE			512		0800 000x	copp cade
				STATE SECTION STATES	7,48					gaap cada	good coop
OCh	PRI	FEFFE	ADIF	التشنيطا		Error to the	Elizabeta de Santo	Salahanda da d	Carried Annie Control		pppp odgp
<b>BC</b> ft	PEI	2005	ADIE		77.0			Marie and		0000 0000	
1Bh	ADRESH	A/D Result	Riccistor i	ich Byta						CHAR WAXX	anna minnn
980	ADRESL.	A/D Result	Register L	ow Byle						XXXX XXXX	mann munn
1Fh	ADCONG	ADC81	ADC80	CHE2	CHS1	CH50	GOYDONE		ADON	0.00 00.0	0000 00-0
			100			PCFG3	PCFG2	PCFG1	PCFGII	0- 0000	p- 0000
MF11	ADCONS	ACIPM								11 1111	11 1111
BALIN .	TRUSA				Date Cirection I			<del></del>			bu coon
ÖBh	PORTA			PORTA	Dela Laloh who	n witten: F				8x 0008	
san(f)	TRISE	100	OF	1000	PHRAGOE	-	PORTE Date	a Ciracton i	Mx	d000 -111	0000 -111
OSHCII	PORTE	_	_	-	-	-	RE2	RET	REO	жжж	

# **Instruction Set Summary:**

Mogre	ric	Description	Cycles	14-Bi	Opcode			Status	Notes
Operat				MSb			L.Sb	Affected	
	_	BYTE-ORIENTED FILE	REGISTER OPE	RATIO	HS				
ADDWF	f, d	Acid W and f	1	0.0	0111	acte		C,DC,Z	1,2
NDWE	ř. d	AND W with f	1	9.0	1101			Z	1,2
LRF	f -	Clear	1	90	3081			Z	2
L ROV		Clear W	1	0.0		XXX		Z.	12
COMF	f. d	Complement f	1	g p		dľfľ		Z	
DECF	f, d	Decrement f	1 1	ap		atit		Z	1,2
DECFSZ	6.4	Degreement f, Skip if 0	1(2)	40	1011	acre		_ :	1,2,3
NCF	ř. d	Incorporat f	1 1	9.0		dere		Z	12
INCFSZ	f, d	Incompet f. Skip f 0	1(2)	<b>3</b> 0		aete		_	1,2,3
IORNE	i d	Inclusive OR W with I	1	0.0	91.00			Z	1,2
MOVE	f, d	Marsa F	1 1	ap		atit		Z	1,2
MOVIE	j, u	Move Yr to f	1	8.0	1010	lere	titi		
NOP		No Operation	1	0.0	1000	OXX 0	9900		
RLF	f. d	Retate Left f through Carry	1 1	ao	1101	dett	titi	C	1,2
REF	f, d	Rotate Right f through Carry	1	ap	1180	dľíľ	etet	С	1.2
	i, d	Subject W from i	l 1	ap	0010	atit	TITI	C.DC.Z	1,2
SUBWF	f. d	Swap nibbles in f	1 1	ap	1110	dere	tttt		1,2
XDRWF	f, d	Exclusive OR W with f	l i	00	01.10	acre	rici	Z	1,2
AURITE	1, 11	BIT-ORIENTED FLE F	SEGISTER OPE	RATION	VIS.				
	f. b	Bit Clear f	1	63	edate	bitt	TETE		12
BCF	1, 10 f, b	Bt Set f	1 1	601	01bb	biti	TETE	l .	1,2
		Bit Test I. Skip if Clear	1 (2)	01	10bb	piti	rrrr		3
BTFSC	f, b		1 20	01	11bb	MILI	tttt	l	3
OTFSS	f, b	Bit Test f, Slep if Set LITERAL AND CO							
			1	1.1	1119	kkkk	kkkk	CDC.Z	T
ACICILIA	k	Acid literal and W	1 1	111	1001		kkkk		
ANDLW	k	AND literal with W	2	1.0	Skirk		kikki	1 -	1
CALL	k	Call subrouting	1 1	00	papa		0100	TOPD	
CLRWOT	•	Clear Watchdog Timer	1 2	110	1kkk		kkkk	,	
GOTO	k	Go to address	1 1	111	1658		kkkk	l z	1
IOSELW	k	Indusive OR literal with W	1 1	111	DOXX	kikiki		l -	1
MOVLY	k	Mave literal to W	1/2	08	0000	4084		1	1
RETFE		Return from interrupt	2	111	DLXX			I	1
RETLW	k	Return with literal in W	1 2	00	DODE	8000	***************************************	l	1
RETURN	-	Raturn from Subroutine	1	an	0000	0110			I
SLEEP	•	Go into standby mode							1
SUELW	k	Subtract W from Iteral	1	11	110x				1
XORLY	k	Exclusive OR Iteral with W	1	11	1010	kkkk	REKE		

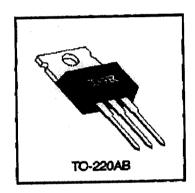
# Field Description:

Field	Description
£	Register file address (0x00 to 0x7F)
X	Working register (accumulator)
ъ	Bit address within an 6-bit file register
k	Literal field, constant data or label
×	Don't care location (= a or 1) The assembler will generate code with $x = p$ , it is the recommended form of use for compatibility with all Microchip software tools.
đ	Destination select; d = o; store result in W, d = 1; store result in file register f. Default is d = 1
PC	Program Counter
TO	Time-out bit
70	Power-down bit

# International IOR Rectifier **IRF840**

# HEXFET® Power MOSFET

- Dynamic dv/dt RatingRepetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements



Absolute Maximum Ratings

	Parameter	Max.	Units
lo	Continuous Drain Current, Vas @ 10 V	8.0	
In @ Tc = 100°C	Continuous Drain Current, Vas @ 10 V	5.1	_ A
low	Pulsed Drain Current ①	32	
Pp <b>6</b> Tc = 25°C	Power Dissipation	125	W
rp w rc-zw v	Linear Derating Factor	1.0	W/°C
Vgs	Gate-to-Source Voltage	±20	<u> </u>
Eas	Single Pulse Avalanche Energy ②	510	mJ
IAR .	Avalanche Current ①	8.0	A
EAR .	Repetitive Avalanche Energy ①	13	<u>mJ</u>
dv/dt	Peak Diode Recovery dv/dt ③	3.5	V/na
Тј Твте	Operating Junction and Storage Temperature Range	-55 to +150	_
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw	10 lbf•ln (1.1 N•m)	

# **Electrical Characteristics:**

	Parameter	Min.	Тур.	Max.	Units	Test Conditions
V <sub>(en)oss</sub>	Drain-to-Source Breakdown Voltage	500		******	٧	V <sub>GS</sub> =0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)OSS</sub> /ΔT <sub>J</sub>	The second secon	T	0.78	_	V/°C	Reference to 25°C, io= 1mA
Ros(on)	Static Drain-to-Source On-Resistance			0.85	Ω	V <sub>GS</sub> =10V, I <sub>D</sub> =4.8A @
Vas(h)	Gate Threshold Voltage	2.0		4.0	ν	VDS=VGS, ID= 250µA
9ts	Forward Transconductance	4.9			S	V <sub>DS</sub> =50V, I <sub>D</sub> =4.8A @
Aue			_	25		V <sub>DS</sub> =500V, V <sub>GS</sub> =0V
loss	Drain-to-Source Leakage Current	_	_	250	μΑ	VD8=400V, VGS=0V, TJ=125°C
	Gate-to-Source Forward Leakage	1 =	_	100	nA	V <sub>GS</sub> =20V
lgs <b>s</b>	Gate-to-Source Reverse Leakage	<b> </b>		-100	117	V <sub>GS</sub> =-20V
Qq	Total Gate Charge		_	63		I <sub>D</sub> =8.0A
Q <sub>gs</sub>	Gate-to-Source Charge	_		9.3	nC	V <sub>DS</sub> =400V
Q <sub>pd</sub>	Gate-to-Drain ("Miller") Charge			32		V <sub>GS</sub> =10V See Fig. 6 and 13 €
tation)	Turn-On Delay Time		14		1	V <sub>00</sub> =250V
t <sub>r</sub>	Rise Time		23		l ns	1 <sub>D</sub> =8.0A
Letjoffj	Turn-Off Delay Time	_	49		]	Rg=9.1Ω
tı	Fall Time	_	20			R <sub>0</sub> =31Ω See Figure 10 @
Lo	Internal Drain Inductance	_	4.5	_	nΗ	Between lead, 6 mm (0.25in.)
Ls ·	Internal Source Inductance	_	7.5	_		from package and center of die contact
Cips	Input Capacitance		1300	_		V <sub>GS</sub> =0V
Com	Output Capacitance	_	310	_	pF	V <sub>06</sub> =25V
Cres	Reverse Transfer Capacitance		120			f=1.0MHz See Figure 5

#### Source-Drain Ratings and Characteristics

	Parameter	Min.	Тур.	Max.	Units	Test Conditions
ls	Continuous Source Current (Body Diode)	-		8.0	Α	MOSFET symbol showing the
law	Pulsed Source Current (Body Diode) ①	_	_	32		integral reverse p-n junction diode.
Vsp	Diode Forward Voltage			2.0	V	Tj=25°C, Is=8.0A, Ves=0V @
ler.	Reverse Recovery Time		460	970	ns	T,=25°C, l==8.0A
Qrr	Reverse Recovery Charge		4.2	8.9	μC	di/dt=100A/µs ④
ton	Forward Turn-On Time	Intrinel	c turn-or	n time is	neglegit	ole (turn-on is dominated by Ls+Lo

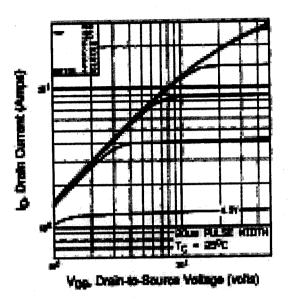


Fig 1. Typical Output Characteristics, To=25°C

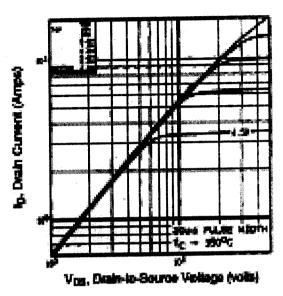


Fig 2. Typical Output Characteristics, To=150°C

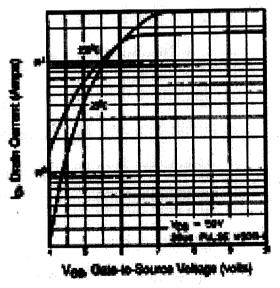


Fig 3. Typical Transfer Characteristics

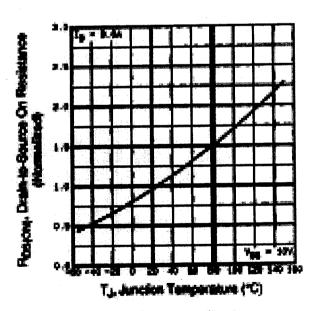


Fig 4. Normalized On-Resisance Vs. Temperature

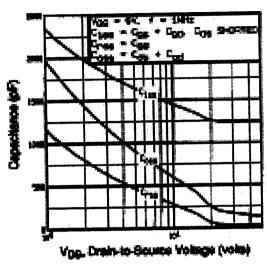


Fig S. Typical Capacitance Vs. Drain-to-Source Voltage

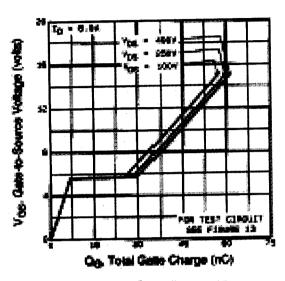


Fig 5. Typical Gate Charge Vs. Gate-to-Source Voltage

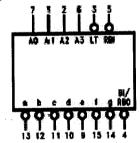


# DM74LS47 BCD to 7-Segment Decoder/Driver with Open-Collector Outputs

#### **Features**

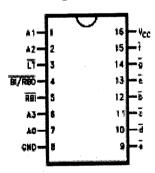
Open-collector outputs
Drive indicator segments directly
Cascadable zero-suppression capability
Lamp test input

#### **Logic Symbol**



V<sub>CC</sub> = Pin 16 GND = Fin 8

## **Connection Diagram**

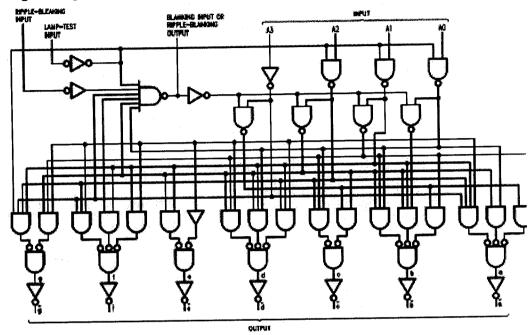


#### **Pin Descriptions**

Pin Names	Description
EA-DA	BCD Inputs
RBI	Ripple Blanking Input (Active LOW)
lत	Lamp Test Input (Active LOW)
BI/RBO	Blanking Input (Active LOW) or
	Ripple Blanking Output (Active LOW)
ā-g	Segment Outputs (Active LOW) (Nate 1)

Note 1: OC-Open Collector

#### Logic Diagram



## Numerical Designations—Resultant Displays



## **Recommended Operating Conditions**

Symbol	Parameter	Win	Nom	Max	Units
V <sub>cc</sub>	Supply Voltage	4.75	5	5.25	٧
/ <sub>IH</sub>	HIGH Level input Voltage	2			V
il.	LOW Level Input Voltage			0.8	V
ОН	HIGH Level Output Current a - g @ 15V = V <sub>CH</sub> (Note 7)			-250	μΑ
OH .	HIGH Level Output Current BI /RBO			-50	μA
OL.	LOW Level Output Current			24	mA
	Free Air Operating Temperature	0		70	°С

Note 7: OFF-State at a-g.

## **Electrical Characteristics**

Symbol	nmended operating free air temperature ran Parameter	Conditions	Min	Typ (Note 8)	Мах	Un its
4	Input Clamp Voltage	V <sub>DC</sub> = Min, I <sub>1</sub> = -18 mA			-1.5	V
QH .	HIGHLeval	V <sub>DC</sub> = Min, I <sub>OH</sub> = Max,	2.7	3.4		٧
	Output Voltage	Vil - Max, Eli (REO				<u> </u>
OFF	Output HISH Current Segment Outputs	V <sub>CC</sub> = 5.5V, V <sub>C</sub> = 15V a - g			250	μΑ
GL	LOW Level	V <sub>CC</sub> = Min, l <sub>CL</sub> = Marx,		0.35	0.5	
	Output Voltage	V <sub>IH</sub> = Min, a – g				
		loL = 32 mA, BI /RBO			0.5	٧
		l <sub>0L</sub> = 12 mA, a -g		0.25	0.4	
		In - 1.6 mA, BIARBO			0.4	
	Input Current @ Max	V <sub>DG</sub> = Max, V <sub>I</sub> = 7V			100	μА
	Irrout Voltage	V <sub>DG</sub> = Max, V <sub>I</sub> = 10V				,
IH	HIGH Level Input Current	V <sub>CC</sub> - Max, V <sub>I</sub> - 27V			20	μA
il.	LOW Level Input Current	Voc - Max, Vi - 0.4V			-0.4	mA
ОВ	Short Circuit	V <sub>CC</sub> - Max (Note 9).				mA
~ ·	Output Current	IOS at BIARBO	-0.3		-2.0	ł
œ	Supply Current	V <sub>DC</sub> = Max			13	mA

Note 8: All typicals are at  $V_{\rm OC}$  = 5V,  $T_{\rm A}$  = 26°C.

Note 8: Not more than one culput should be shorted at a time, and the curation should not exceed one second.

# **Switching Characteristics**

at V~ = +5.0V. T4 = +25°C

[ CL = 15	C <sub>L</sub> = 15 pF	
Min	Max	1
	100	ns
	100	'"
	100	1
	100	ns
		Min Mex 100 100 100

Note 10: T = HIGH, A0-A3 = LOW



#### CD4066BC Quad Bilateral Switch

#### **Features**

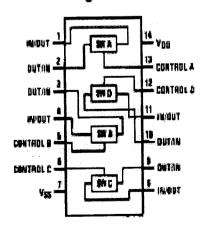
- Wide supply voltage range 3V to 15V
- High noise immunity 0.45 VDD (typ.)
- Wide range of digital and ±7.5 VPEAK analog switching
- "ON" resistance for 15V operation 80.
- \_ Matched "ON" resistance .RON = 5. (typ.)

over 15V signal input

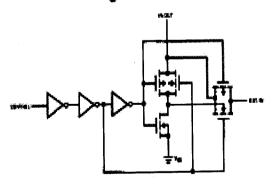
- "ON" resistance flat over peak-to-peak signal range
- High "ON"/"OFF" 65 dB (typ.)

output voltage ratio @ fis = 10 kHz, RL = 10 k.

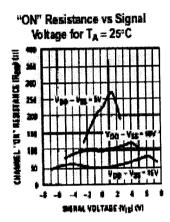
#### **Connection Diagram**

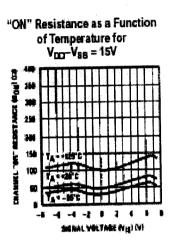


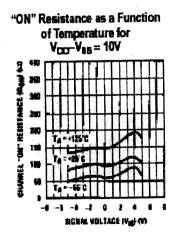
#### **Schematic Diagram**

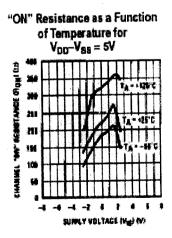


# **Typical Performance Characteristics**









#### LM78XX 1.5A Positive Voltage Regulator

#### **Features**

- Output Current of 1.5A
- Output Voltage Tolerance of 5%
- Internal thermal overload protection
- Internal Short-Circuit Limited
- No External Component
- Output Voltage 5.0V, 6V, 8V, 9V, 10V, 12V, 15V, 18V, 24V
- Offer in plastic TO-252, TO-220 & TO-263
- Direct Replacement for LM78XX

#### **Packaging Information**





- 1. Input
- 2. GND
- 3. Output

Absolute Maximum Rating

Parameter		LM78	Unit
	LM7824, LM7827	40	V
Input Voltage	All Others	35	
Operating Free-Air, Case, Virtual Junction Temp.		0 to 150	°C
Storage Temperature R		-65 to 150	]
Lead temperature 1.6 m	m from case for sec.	260	

Electrical Characteristics (LM7805) (V<sub>1</sub>=10V, I<sub>0</sub>=500mA, 0°C ≤T<sub>3</sub>≤125 °C, unless otherwise specified. (Note 1)

The same of the	Sumbol	Conditions	MIN	TYP	MAX	UNIT
Parameter		T <sub>1</sub> = 25 °C	4.8	5,0	5.2	V
Output Voltage	V <sub>o</sub>			3	100	mV
Line Regulation	ΔVo	$V_t = 7V \text{ to } 25V \text{ T}_1 = 25 \text{ °C}$		+-	50	i
		$V_1 = 8V \text{ to } 12V T_1 = 25 \text{ °C}$		+	100	mV
Load Regulation	ΔV <sub>Q</sub>	I <sub>o</sub> = 5mA to 1.5A, 25 °C		15		l "" \
	-	I <sub>o</sub> =250mA to 750mA, 25 °C		5	50	
Ripple Rejection	RR	V <sub>t</sub> = 8V to 18V, f=120Hz	62	78	ļ	dB
Output Noise Voltage	V <sub>N</sub>	F= 10Hz to 100Hz T <sub>f</sub> = 25 °C	erra:	40		μV
Dropout Voltage	Vo	T <sub>1</sub> = 25 °C		2.0		V
Quiescent Current		T <sub>1</sub> = 25 °C		4,2	8	mA
Quiescent Current	ΔLo	V <sub>1</sub> = 7V to 25V, T <sub>2</sub> = 25 °C			1,3	mA
Change		$I_0 = 5$ mA to IA, $T_1 = 25$ °C			0,5	

#### **Electrical Characteristics (LM7812)**

(V<sub>1</sub>=19V, I<sub>0</sub>=500mA, 0°C ≤T<sub>1</sub>≤125 °C, unless otherwise specified. (Note 1)

Parameter	Sambal	Conditions	MIN	TYP	MAX	UNIT
Output Voltage	Vo	T. = 25 °C	11.50	12	12.5	V
Line Regulation	ΔVo	$V_t = 14.5 \text{V to } 30 \text{V T}_t = 25 \text{ °C}$		10	240	mV
Time KeRtranon	2.70	V <sub>1</sub> = 16V to 22V T <sub>2</sub> = 25 °C		3,0	120	
Load Regulation	$\Delta V_{ci}$	I <sub>O</sub> = 5mA to 1.5A, 25 °C		12	240	m.V
		I <sub>o</sub> =250mA to 750mA, 25 °C		4	120	
Ripple Rejection	RR	V <sub>1</sub> = 15V to 25V, f=120Hz	55	71	<u> </u>	dB
Output Noise Voltage	V <sub>N</sub>	F= 10Hz to 100Hz TJ= 25 °C		75		μV
Dropout Voltage	Vp	T,=25 °C		2,0		<u> </u>
Ouicecent Current		T.= 25 °C		4,3	8.0	m A
Quiescent Current	ΔĬο	$V_t = 14.5 \text{V to } 30 \text{V}, T_f = 25 ^{\circ}\text{C}$			1.0	mA.
Change		I <sub>O</sub> = 5mA to 1A, T <sub>J</sub> = 25 °C			0,5	